

Amendments to the specification

Page 1, from line 9, please amend as follows:

91

RIE (reactive ion etching) has long been used in a metallization step for semiconductor devices. In such a step, deposits of a reaction product called, "polymer" or "wall pieces" remains on a surface of an etched substrate. A polymer stripper treatment step has, therefore, been needed to remove the deposits after the etching. Many of chemicals useful in the polymer stripper treatment step have high viscosity and are expensive, and a significant load is required for the treatment of waste water. Such chemicals are, therefore, circulated and reused in many instances. To permit effective handling of a chemical the composition of which tends to vary due to evaporation or the like, the treatment with the chemical as a polymer stripper is widely conducted by suitably supplying the chemical from a circulating tank onto a surface of a substrate only when the treatment is conducted rather than a bath-type treatment that a substrate is dipped in the chemical. To meet requirements for this treatment, a variety of treatment apparatuses have been developed, including single-wafer or batch processing apparatuses and apparatuses equipped with a mechanism for spraying a chemical onto plural substrates while causing the substrates to rotate (or eccentrically rotate) or to revolve (see ~~US patent no. 4,132,567 that issued on January 2, 1979, (1979/1/2, year/month/day), US patent no. 626702 (1984/7/2), and US patent no. 626640 (1984/7/2))~~ U.S. Patent No. 4,132,567 that issued on January 2, 1979, U.S. Patent No. 4,682,615 (Ser. No. 626,702 filed on July 2, 1984), and U.S. Patent No. 4,609,575 (Ser. No. 626,640 filed on July 2, 1984))).

Page 43, from line 2, please amend as follows:

92

A wet treatment method ~~useful in~~ for at least one of a chemical processing step

and a rinsing step performed upon fabrication of semiconductor devices is disclosed.

Q2
~~According to this method, a~~ A substrate under treatment is treated with a desired liquid while causing the substrate to revolve around an axis of rotation outside the substrate itself instead of allowing the substrate to rotate about the axis of rotation such that the liquid flowing on a surface of the substrate is maintained flowing under a centrifugal force greater than gravitation. The substrate is treated while supplying a fresh liquid of the same kind as the desired liquid at a flow rate at least equal to a discharge rate of the desired liquid only in a direction conforming with that of the centrifugal force or with that of a flow of the liquid flowing on the surface of the substrate under the centrifugal force. The substrate is, therefore, evenly treated at the surface thereof with the desired liquid while avoiding development of such a situation that flows of the liquid run against each other on the surface of the substrate or a flow of the liquid stagnates on the surface of the substrate. A wet treatment apparatus suitable for use in practicing the wet treatment method is also disclosed.
